

BASE

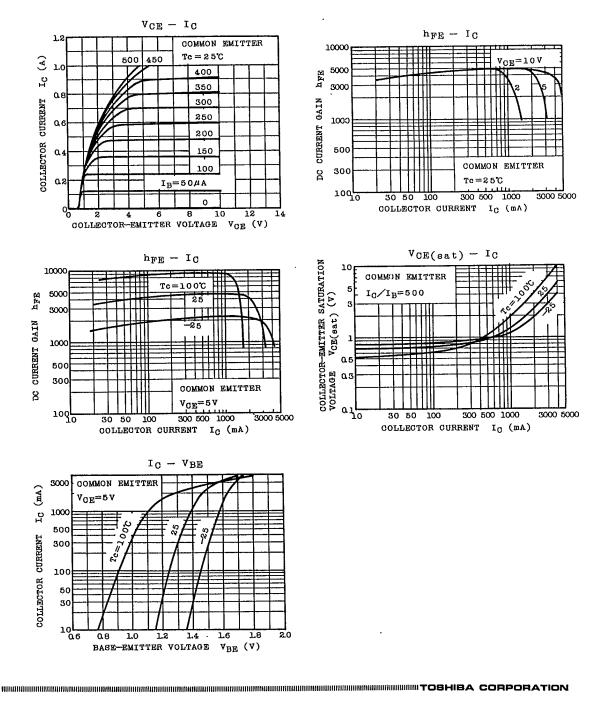
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V(BR)CBO	I _C =10mA, I _E =0	45	60	75	v
Collector-Emitter Breakdown Voltage	V (BR) CEO	IC=100mA, IB=0	45	60	75	v
Emitter Cut-off Current	IEBO	V _{EB} =6V, I _C =0	-	-	100	μA
DC Current Gain	hFE	VCE=5V, IC=0.5A	2000	-	20000	
Collector-Emitter Saturation Voltage	V _{CE(sat)} (1)	I _C =0.5A, I _B =1mA .	. –	-	1.5	V.
Collector-Emitter Saturation Voltage	V _{CE(sat)} (2)	I _C =1A, I _B =1mA	-	-	2.5	v
Base-Emitter Voltage	VBE	V _{CE} =5V, I _C =0.5A	-	-	1.8	V
Allowable Energy (Tc=25 ^o C)	ET	Application Circuit	100	-	-	W·sec

-820-

56C 07888 DT-33-13

2SD1208

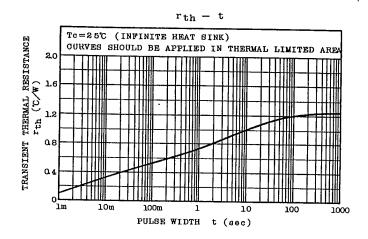


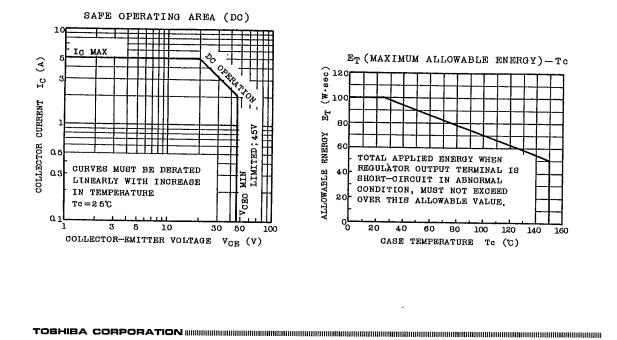
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TOSHIBA {DISCRETE/OPTO}

9097250 TOSHIBA (DISCRETE/OPTO)

2SD1208

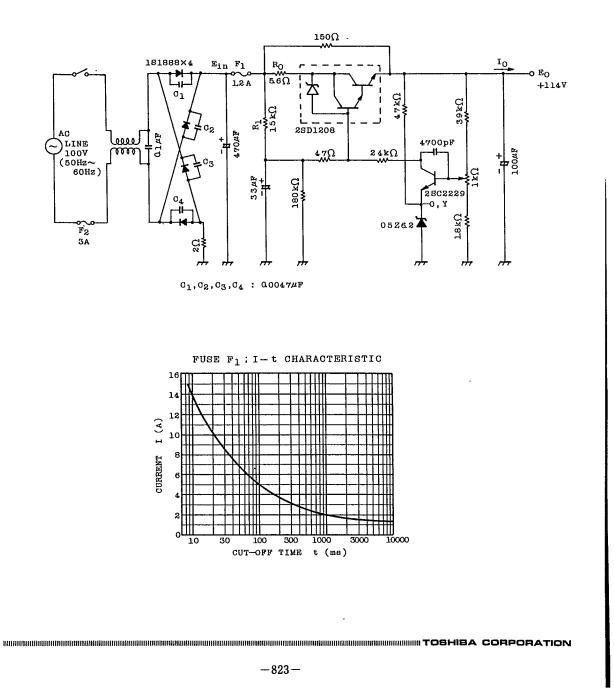




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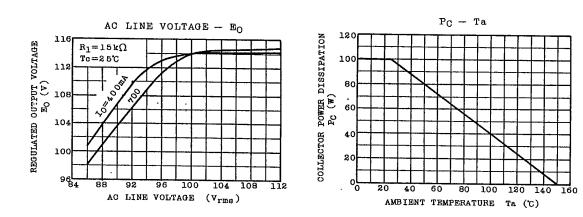
TOSHIBA {DISCRETE/OPTO}	56 DE 9097250 0007890 3
9097250 TOSHIBA (DISCRETE/OPTO)	56C 07890 D T-33-13 2SD1208

APPLICATION CIRCUIT



9097250 TOSHIBA (DISCRETE/OPTO) 2SD1208





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